

IN THE CLAIMS:

Please amend claims 17, 18, 20, 45, 47, 49 and 52 as follows. Attached hereto is a marked-up copy of claims 17, 18, 20, 45, 47, 49 and 52 in their amended form.

a' 17. (Amended) A method for the manufacture of a semiconductor device comprising:

a step of preparing a substrate in which a surface thereof is formed a depression having a triangle or hexagonal figure when viewed from the substrate normal; and

a step of forming on said surface of said substrate a semiconductor layer having a hexagonal crystal structure,

wherein said depression forming step is performed such that an inside face of said depression is defined by either a plane having a plane orientation of $(1, -1, 0, n)$, where said number n is an arbitrary number other than 0, or its equivalent plane.

Pub B2 18. (Amended) A method for the manufacture of a semiconductor device comprising:

a step of preparing a substrate;

a step of forming on a surface of said substrate a depression having a triangle or hexagonal figure when viewed from the substrate normal; and

a step of forming on said surface of said substrate a semiconductor layer having a hexagonal crystal structure,

*a¹ amended.
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wherein said depression forming step is performed such that an inside face of said depression is defined by either a plane having a plane origination of (1, -1, 0, n), where said number n is an arbitrary number other than 0, or its equivalent plane.

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20. (Amended) The manufacture method of claim 19,
wherein said depression forming step includes a step of forming on said surface of said substrate defined by a (0, 0, 0, 1) plane a depression having a bottom face whose figure is either an equilateral triangle or an equilateral hexagon.

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45. (Amended) The manufacture method of claim 44,
wherein said exposing step includes a step of applying onto said first semiconductor layer a resist pattern having an opening whose figure is either substantially an equilateral triangle, or substantially an equilateral hexagon when viewed from the substrate normal; and
a step of forming a depression by subjecting said first semiconductor layer to an etching process in which said resist pattern is used as a mask so that said depression has an inside face comprising either a plane having a plane orientation of (1, -1, 0, n) where said number n is an arbitrary number, or its equivalent plane.

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47. (Amended) The manufacture method of claim 44,
wherein said exposing step includes a step of applying onto said first semiconductor layer a resist pattern whose figure is either substantially an equilateral triangle, or substantially an equilateral hexagon when viewed from the substrate normal; and
a step of forming a projection by subjecting said first semiconductor layer to an etching process in which said resist pattern is used as a mask so that said projection has a side face

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comprising either a plane having a plane orientation of $(1, -1, 0, n)$ where said number n is an arbitrary number or its equivalent plane.

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49. (Amended) A method for the manufacture of a semiconductor substrate comprising:

a step of forming a substrate having on a surface thereof a depression having a triangle or hexagonal figure when viewed from the substrate normal;

a step of forming on said surface of said substrate a semiconductor layer having a hexagonal crystal structure; and

a step of taking out said semiconductor layer by removal of said substrate,

wherein said depression has an inside face defined by either a plane having a plane orientation of $(1, -1, 0, n)$, where said number n is an arbitrary number other than 0, or its equivalent plane.

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52. (Amended) A method for the manufacture of a semiconductor substrate comprising;

a step of forming a substrate having on a surface thereof a triangle or hexagonal projection;

a step of forming on said surface of said substrate a semiconductor layer having a hexagonal crystal structure; and

a step of taking out said semiconductor layer by removal of said substrate,

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wherein said projection has a ~~side~~ face defined by either a plane having a plane orientation of $(1, -1, 0, 1)$, wherein said number n is an arbitrary number other than 0, or its equivalent plane.